

DESCRIPTION

SMC4923DM is the Dual P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance. This device is ideal for load switch applications.

PART NUMBER INFORMATION

SMC **4923D** **M** - **TR** **G**
 a b c d e

- a : Company name.
- b : Product Serial number.
- c : Package code M:SOP-8
- d : Handling code TR:Tape&Reel
- e : Green produce code G:RoHS Compliant

FEATURES

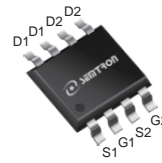
$V_{DS}=-30V$, $I_D=-9.2A$

- $R_{DS(ON)}=11m\Omega(Typ.)@V_{GS}=-20V$
- $R_{DS(ON)}=12m\Omega(Typ.)@V_{GS}=-10V$
- $R_{DS(ON)}=15.5m\Omega(Typ.)@V_{GS}=-4.5V$

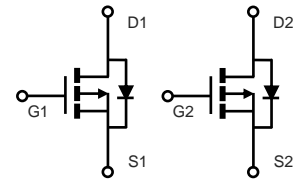
- ◆Fast switch
- ◆High power and current handling capability

APPLICATIONS

- ◆High Frequency Point-of-Load Synchronous
- ◆DC-DC Power System
- ◆Load Switch



SOP-8



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ Unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 25	V
I_D	Continuous Drain Current ($V_{GS}=-10V$)	$T_A=25^\circ C$	-9.2
		$T_A=70^\circ C$	-7.3
I_{DM}	Pulsed Drain Current ^B	-36.8	A
I_{AS}	Avalanche Current ^B	-30	A
E_{AS}	Single Pulse Avalanche energy $L=0.1mH$ ^B	45	mJ
P_D	Power Dissipation ^A	$T_A=25^\circ C$	2
		$T_A=70^\circ C$	1.3
T_J	Operation Junction Temperature	-55/150	$^\circ C$
T_{STG}	Storage Temperature Range	-55/150	$^\circ C$

THERMAL RESISTANCE

Symbol	Parameter	Typ	Max	Units
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ^A	$t \leq 10s$	62	$^\circ C/W$
	Thermal Resistance Junction to Ambient ^{AC}	Steady-State	90	

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

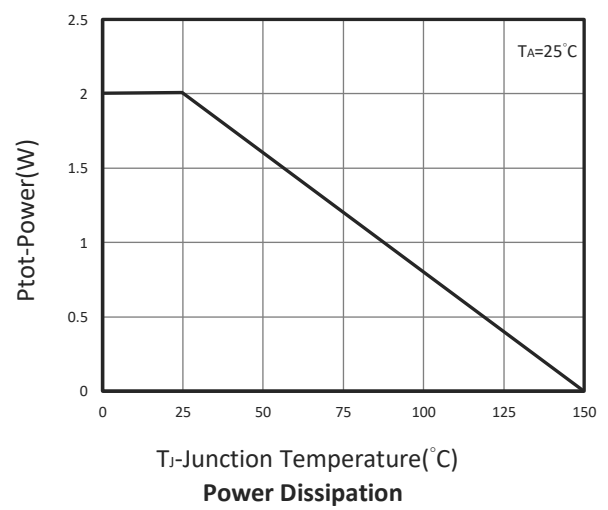
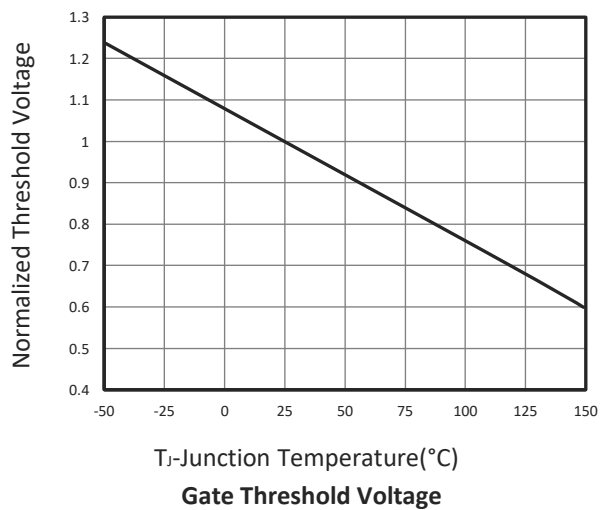
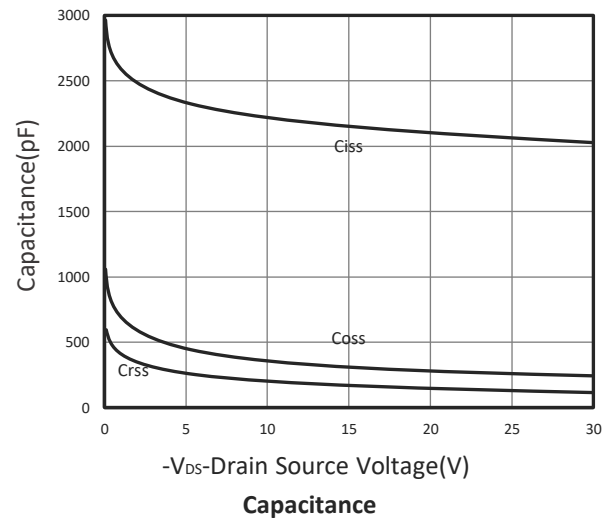
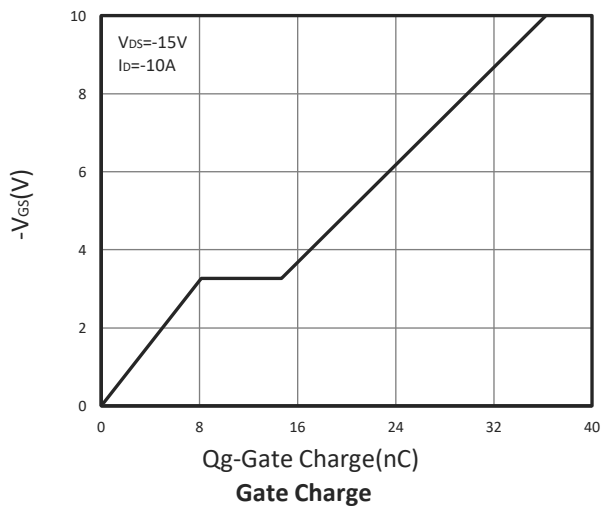
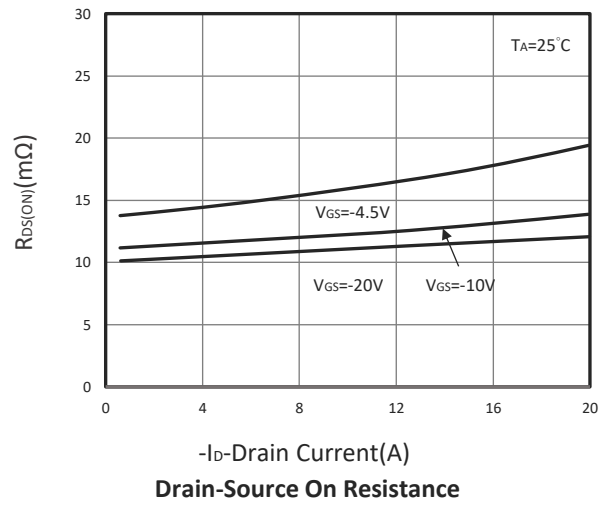
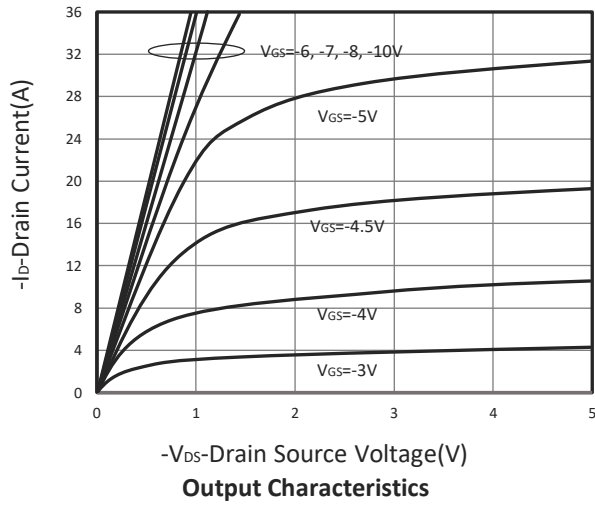
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μ A	-30			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250 μ A	-1	-1.6	-2.5	V
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} = \pm 25V			\pm 100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-30V, V _{GS} =0V, T _J =25 $^\circ$ C			-1	μ A
		V _{DS} =-24V, V _{GS} =0V, T _J =75 $^\circ$ C			-10	
R _{DS(ON)}	Drain-source On-Resistance ^D	V _{GS} =-20V, I _D =-9.2A		11	13	m Ω
		V _{GS} =-10V, I _D =-9.2A		12	15	
		V _{GS} =-4.5V, I _D =-6A		15.5	19	
G _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-10A		12.5		S
Diode Characteristics						
V _{SD}	Diode Forward Voltage ^D	I _S =-1A, V _{GS} =0V		-0.7	-1	V
I _S	Diode Continuous Forward Current				-9	A
t _{rr}	Reverse Recovery Time	I _S =-10A, dI/dt=100A/ μ s		13.8		ns
Q _{rr}	Reverse Recovery Charge			11.6		nC
Dynamic and Switching Parameters^E						
Q _g	Total Gate Charge	V _{DS} =-15V, V _{GS} =-10V I _D =-10A		36	48.6	nC
Q _g	Total Gate Charge (4.5V)			18	24.3	
Q _{gs}	Gate-Source Charge			8.1	10.9	
Q _{gd}	Gate-Drain Charge			6.8	9.2	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz		2150		pF
C _{oss}	Output Capacitance			298		
C _{rss}	Reverse Transfer Capacitance			135		
R _g	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		8.8		Ω
t _{d(on)}	Turn-On Time	V _{DD} =-15V, V _{GEN} =-10V R _G =3.3 Ω , I _D =-1A		7.7	15	nS
t _r				57.8	129	
t _{d(off)}	Turn-Off Time			57.5	109	
t _f				21.3	40	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

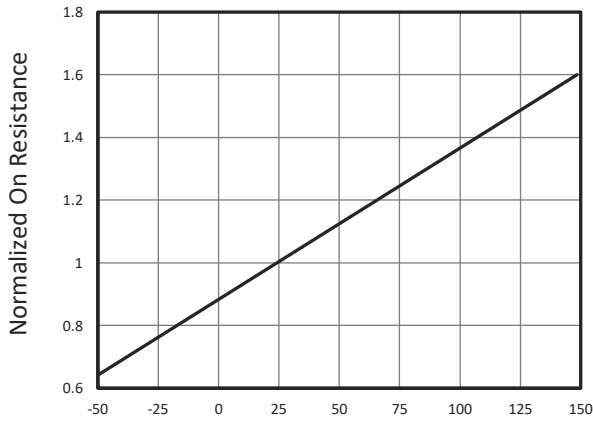
- A. Surface mounted on FR4 board using 1 in² pad size.
- B. Pulsed width limited by maximum junction temperature, T_{J(MAX)}=150 $^\circ$ C.
- C. Using \leq 10s junction-to-ambient thermal resistance is base on T_{J(MAX)}=150 $^\circ$ C.
- D. Pulse test width \leq 300 μ s and duty cycle \leq 2%.
- E. Guaranteed by design, not subject to production testing.

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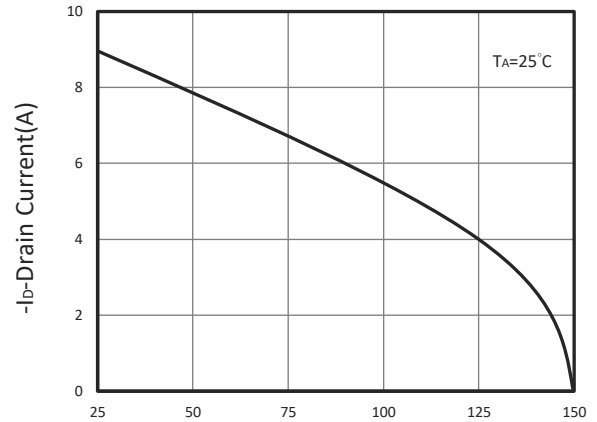
TYPICAL CHARACTERISTICS



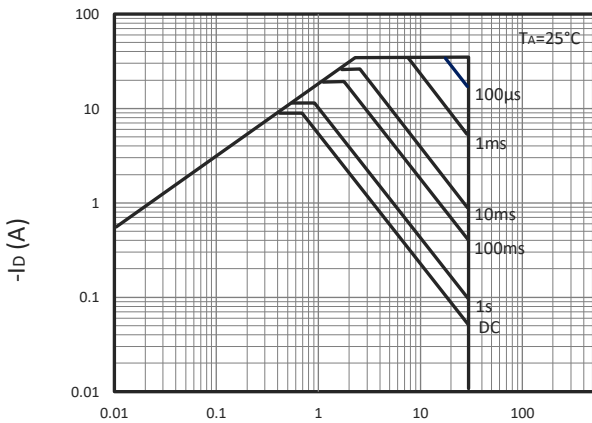
TYPICAL CHARACTERISTICS



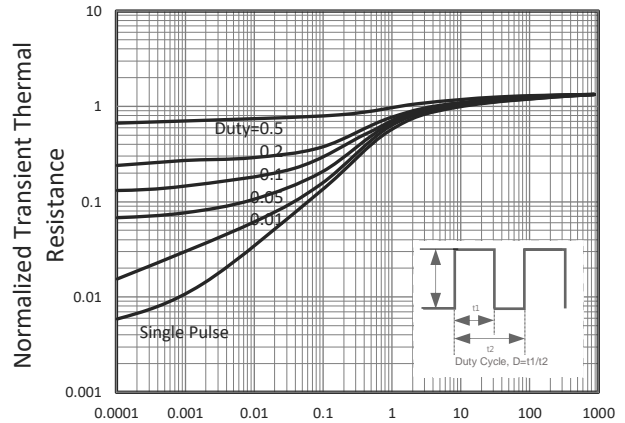
$R_{DS(on)}$ vs Junction Temperature



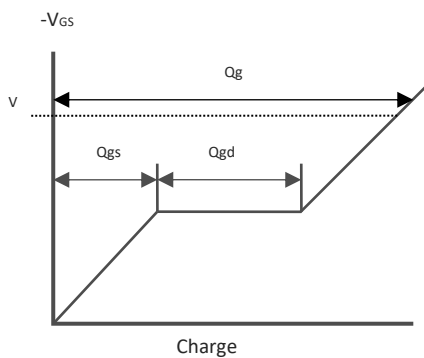
Drain Current vs T_j



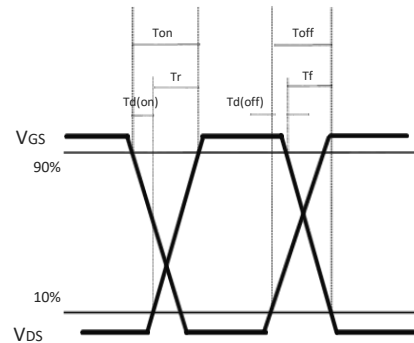
Maximum Safe Operation Area



Thermal Transient Impedance

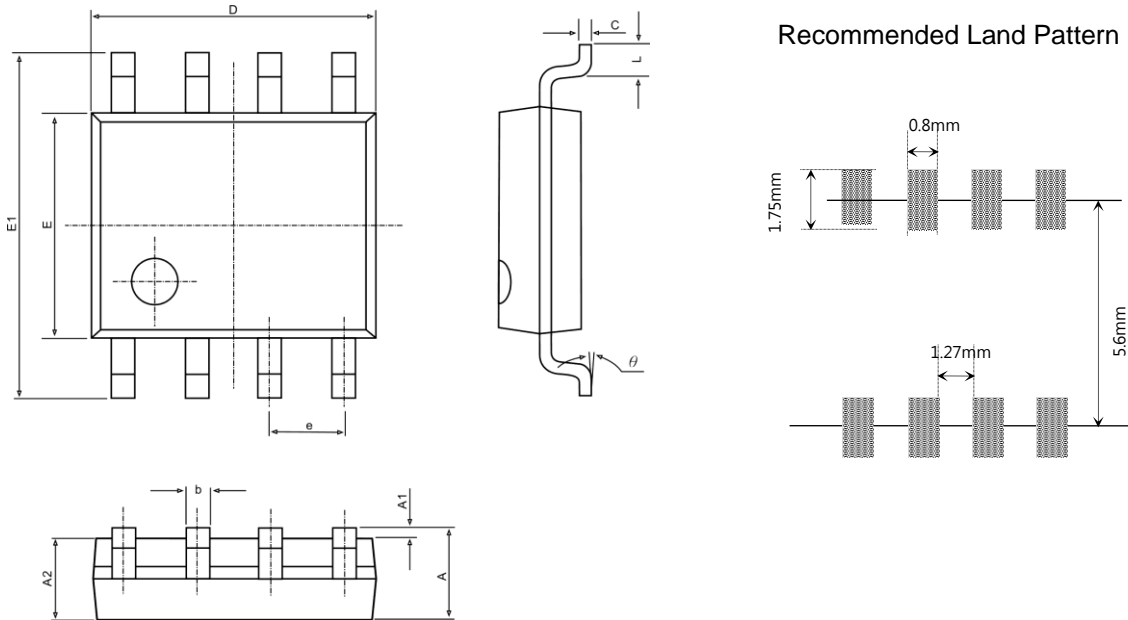


Gate Charge Waveform



Switching Time Waveform

■ SOP-8 PACKAGE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.300	1.500	0.051	0.059
b	0.390	0.490	0.015	0.019
c	0.200	0.250	0.008	0.010
D	4.800	5.100	0.189	0.201
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 BSC		0.050 BSC	
L	0.500	0.800	0.020	0.031
θ	0°	8°	0°	8°